

RF power transistor - LdmoST family

Preliminary Data

Features

- Excellent thermal stability
- Common source configuration
- $P_{OUT} = 25\text{ W}$ with 16 dB gain @ 945 MHz / 13.6 V
- BeO free package
- ESD protection
- In compliance with the 2002/95/EC european directive

Description

The PD85025C is a common source N-channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 13.6 V in common source mode at frequencies of up to 1 GHz. PD85025C boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology.

PD85025C's superior linearity performance makes it an ideal solution for mobile application.

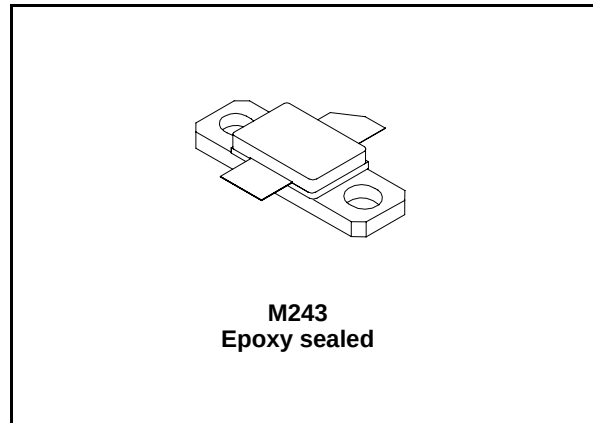


Figure 1. Pin connection

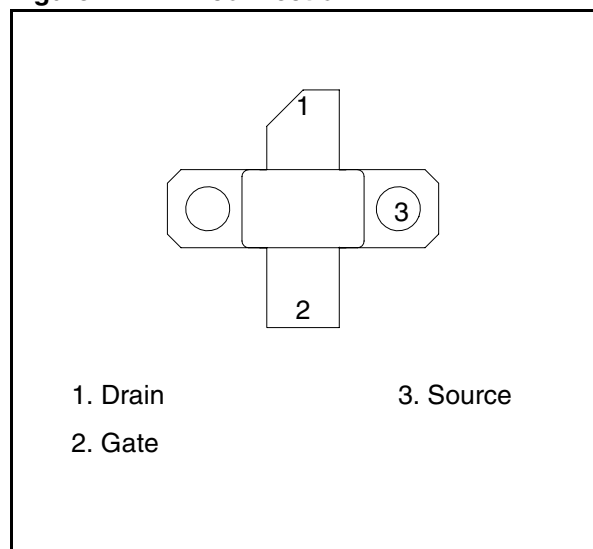


Table 1. Device summary

Order code	Package	Packing
PD85025C	M243	Box

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1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings ($T_{CASE} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current	7	A
P_{DISS}	Power dissipation (@ $T_C = 70^{\circ}C$)	93	W
T_J	Max. operating junction temperature	200	$^{\circ}C$
T_{STG}	Storage temperature	-65 to +150	$^{\circ}C$

1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Junction - case thermal resistance	1.4	$^{\circ}C/W$

2 Electrical characteristics

$$T_{\text{CASE}} = +25\text{ }^{\circ}\text{C}$$

2.1 Static

Table 4. Static

Symbol	Test conditions		Min	Typ	Max	Unit
I_{DSS}	$V_{\text{GS}} = 0\text{ V}$	$V_{\text{DS}} = 25\text{ V}$			1	μA
I_{GSS}	$V_{\text{GS}} = 20\text{ V}$	$V_{\text{DS}} = 0\text{ V}$			1	μA
$V_{\text{GS(Q)}}$	$V_{\text{DS}} = 10\text{ V}$	$I_{\text{D}} = \text{TBD mA}$		TBD		V
$V_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{ V}$	$I_{\text{D}} = 1\text{ A}$		270	310	mV
C_{ISS}	$V_{\text{GS}} = 0\text{ V}$	$V_{\text{DS}} = 12.5\text{ V}$		49		pF
C_{OSS}	$V_{\text{GS}} = 0\text{ V}$	$V_{\text{DS}} = 12.5\text{ V}$		35		pF
C_{RSS}	$V_{\text{GS}} = 0\text{ V}$	$V_{\text{DS}} = 12.5\text{ V}$		1.0		pF

2.2 Dynamic

Table 5. Dynamic

Symbol	Test conditions	Min.	Typ.	Max.	Unit
P3dB	$V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 300\text{ mA}$ $f = 945\text{ MHz}$	25	30		W
G_{P}	$V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 300\text{ mA}$, $P_{\text{OUT}} = 10\text{ W}$, $f = 945\text{ MHz}$	15	17.5		dB
h_{D}	$V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 300\text{ mA}$, $P_{\text{OUT}} = \text{P3dB}$, $f = 945\text{ MHz}$	60	73		%
Load mismatch	$V_{\text{DD}} = 17\text{ V}$, $I_{\text{DQ}} = 300\text{ mA}$, $P_{\text{OUT}} = 45\text{ W}$, $f = 945\text{ MHz}$ All phase angles	20:1			VSWR

2.3 ESD protection characteristics

Table 6. ESD protection characteristics

Test conditions	Class
Human body model	2
Machine model	M3

3 Impedance

Figure 2. Current conventions

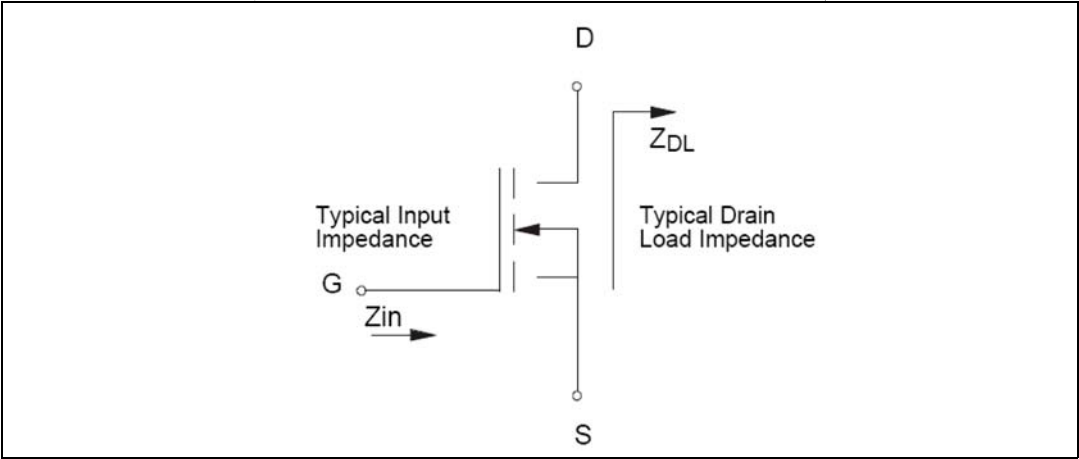


Table 7. Impedance data

Freq. (MHz)	$Z_{IN} (\Omega)$	$Z_{DL}(\Omega)$
945 MHz	$1.01 + j\ 2.03$	$1.75 + j\ 2.20$

4 Typical performance

Figure 3. Capacitances vs drain voltage

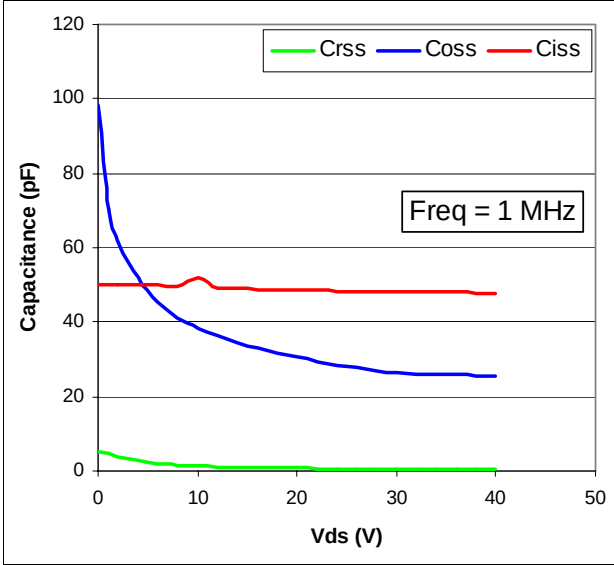


Figure 4. DC output characteristics

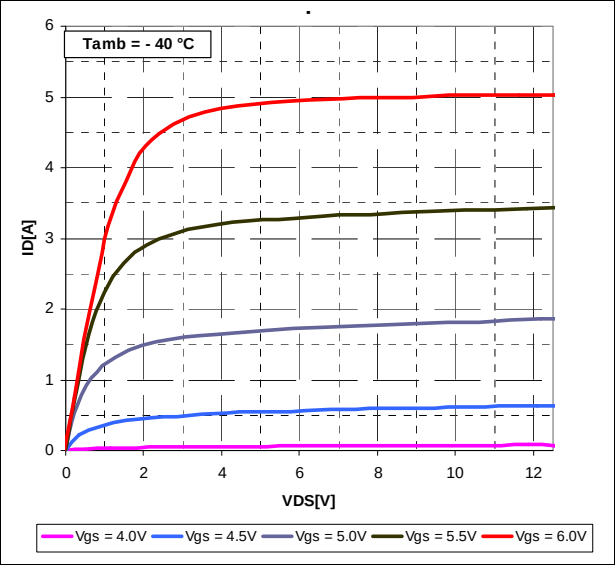


Figure 5. DC output characteristics

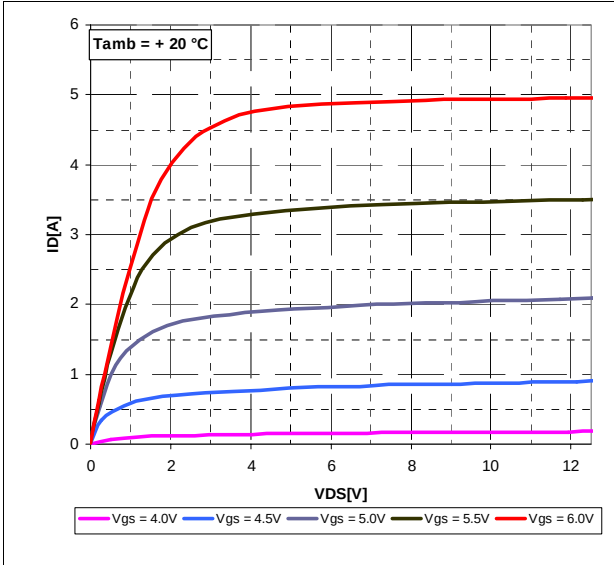


Figure 6. DC output characteristic

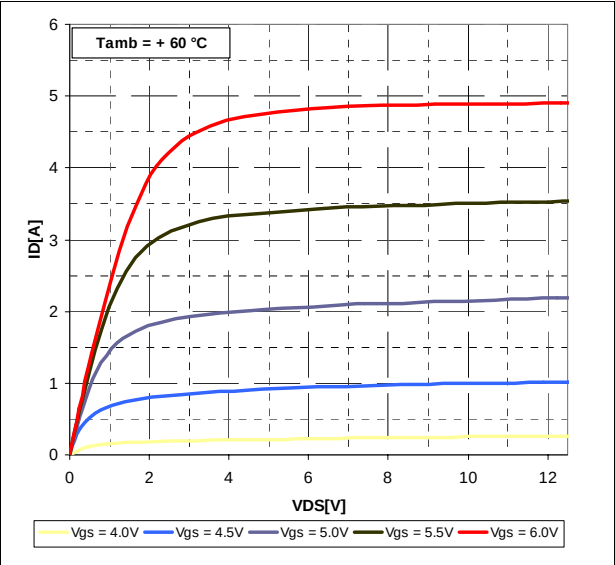


Figure 7. Output power and efficiency vs input power

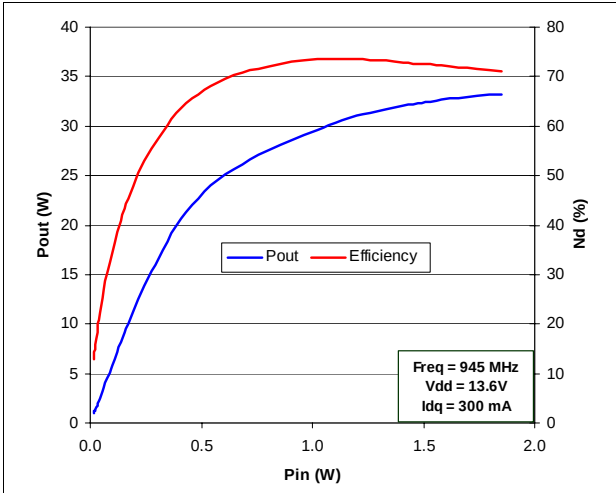


Figure 8. Gain vs output power and bias current

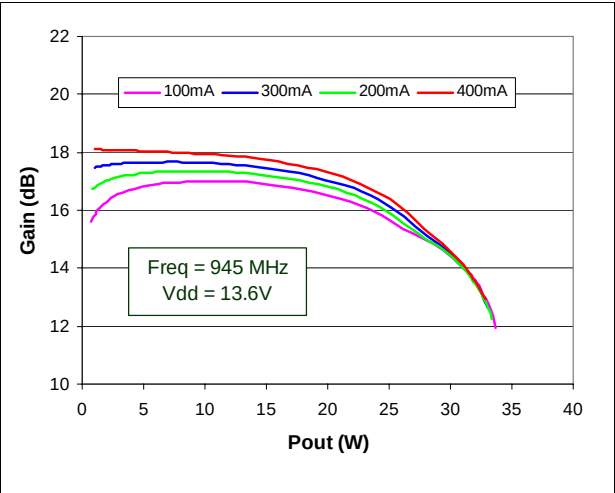


Figure 9. Pout and drain current vs gate voltage

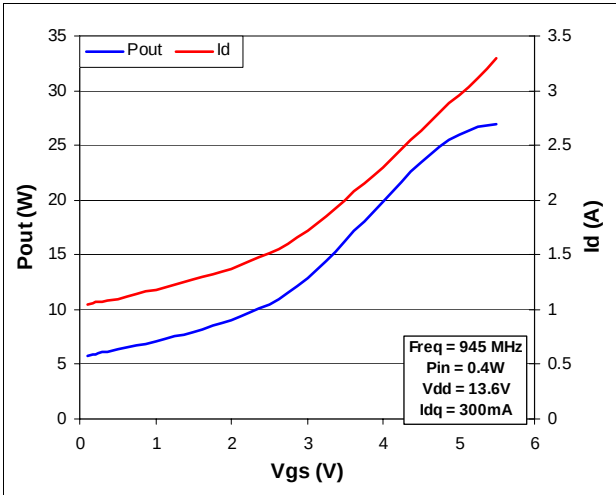


Figure 10. Pout and drain current vs supply voltage

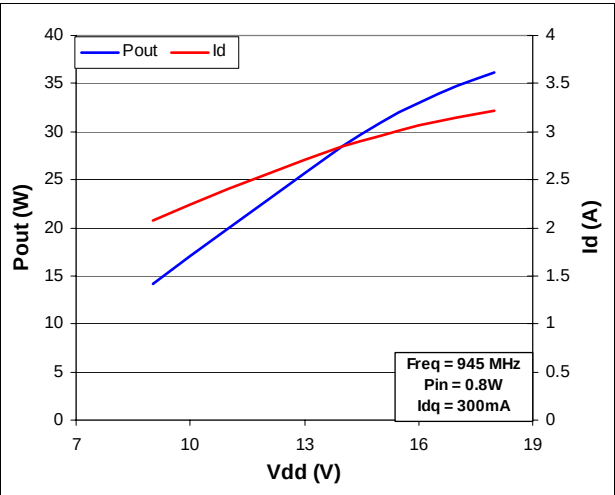
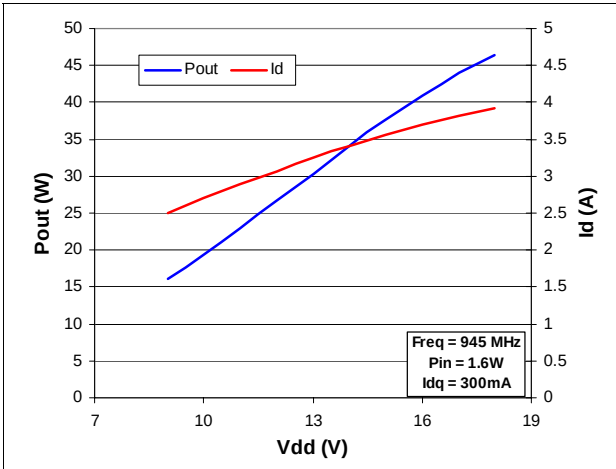


Figure 11. Pout and drain current vs supply voltage



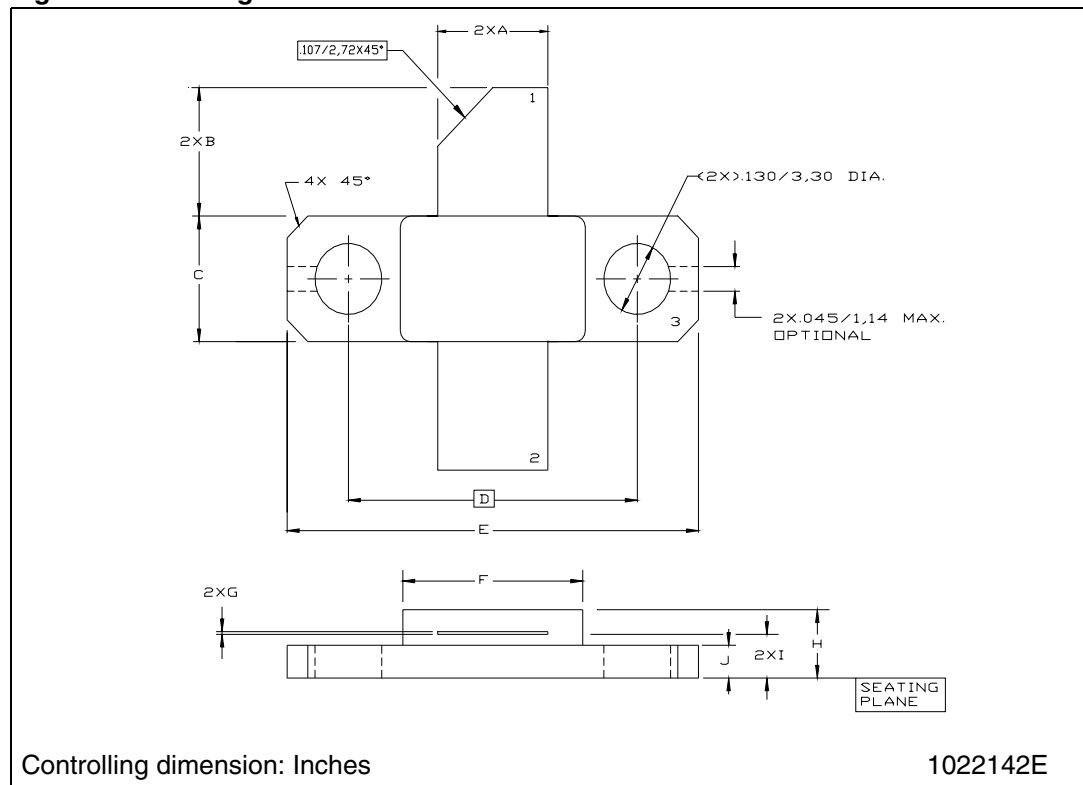
5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Table 8. M243 (.230 x .360 2L N/HERM W/FLG) mechanical data

Dim.	mm.			Inch		
	Min	Typ	Max	Min	Typ	Max
A	5.21		5.72	0.205		0.225
B	5.46		6.48	0.215		0.255
C	5.59		6.10	0.220		0.240
D		14.27			0.562	
E	20.07		20.57	0.790		0.810
F	8.89		9.40	0.350		0.370
G	0.10		0.15	0.004		0.006
H	3.18		4.45	0.125		0.175
I	1.83		2.24	0.072		0.088
J	1.27		1.78	0.050		0.070

Figure 12. Package dimensions



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
10-Dec-2007	1	Initial release.

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